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# Quarterly Technical Progress Report

No. 6329-12

on the

## DEVELOPMENT OF METALLIZATION PROCESS

FSA Project, Cell and Module Formation Research Area

For the Period Ending

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Contract 956205

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The JPL Flat Plate Solar Array Project is sponsored by the U.S. Department of Energy and forms part of the Solar Photovoltaic Conversion Program to initiate a major effort toward the development of low-cost solar arrays. This work was performed for the Jet Propulsion Laboratory, California Institute of Technology by agreement between NASA and DOE.

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#### ABSTRACT/SUMMARY

The use of CO in place of H<sub>2</sub> for the reducing step did not appreciably increase solderability of interconnects. Cells were also made printing the pastes on top of ITO coatings. Some of these cells were the best electrically but the metallization was still not adhering. Sequential use of H<sub>2</sub> and CO had no effect on adhesion (or lack of it).

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## Section 1.0

### INTRODUCTION

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The objective of this contract is the optimization, evaluation, and demonstration of novel metallization applied by a screen-printing process. The process will be evaluated on both CZ and non-CZ silicon wafers.

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## Section 2.0

### TECHNICAL DISCUSSION

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Carbon monoxide has been plumbed into the reducing furnace, allowing the use of either hydrogen or carbon monoxide. Several experiments have been run using the CO.

Carbon monoxide reductions were done after oxidative firings at both 550 and 600°C. There was little difference between the results. The cells were then fired at 550, 600, 625, 650, and 700°C. All cells showed high series resistance and poor curve shape. Figure 1 shows a typical cell air-fired at 600°C 18"/min. and reduced at 625°C for 7.5 minutes. These conditions seemed optimum but the characteristics are unacceptable. There was no appreciable lowering of the shunt resistance even when temperatures of 700°C were reached. Figure 2 shows a cell reduced at 700°C for 10 minutes where little shunting has occurred. Reducing for longer times at lower temperatures increased the series resistance as is seen in Figure 3. Cells fired at the longer times (>15 min.) also had small tin globules formed on the surface.

All cells made with the Type F paste (Pb/borosilicate frit) passed tape-pull tests. Cells made with the Type A paste failed. Soldering was always unsuccessful.

Wafers were coated with indium tin oxide (ITO) prior to metallization. The ITO was applied using reactive sputtering by Applied Film Labs Inc. The thickness varied from 512 to 783Å with an

Figure 1

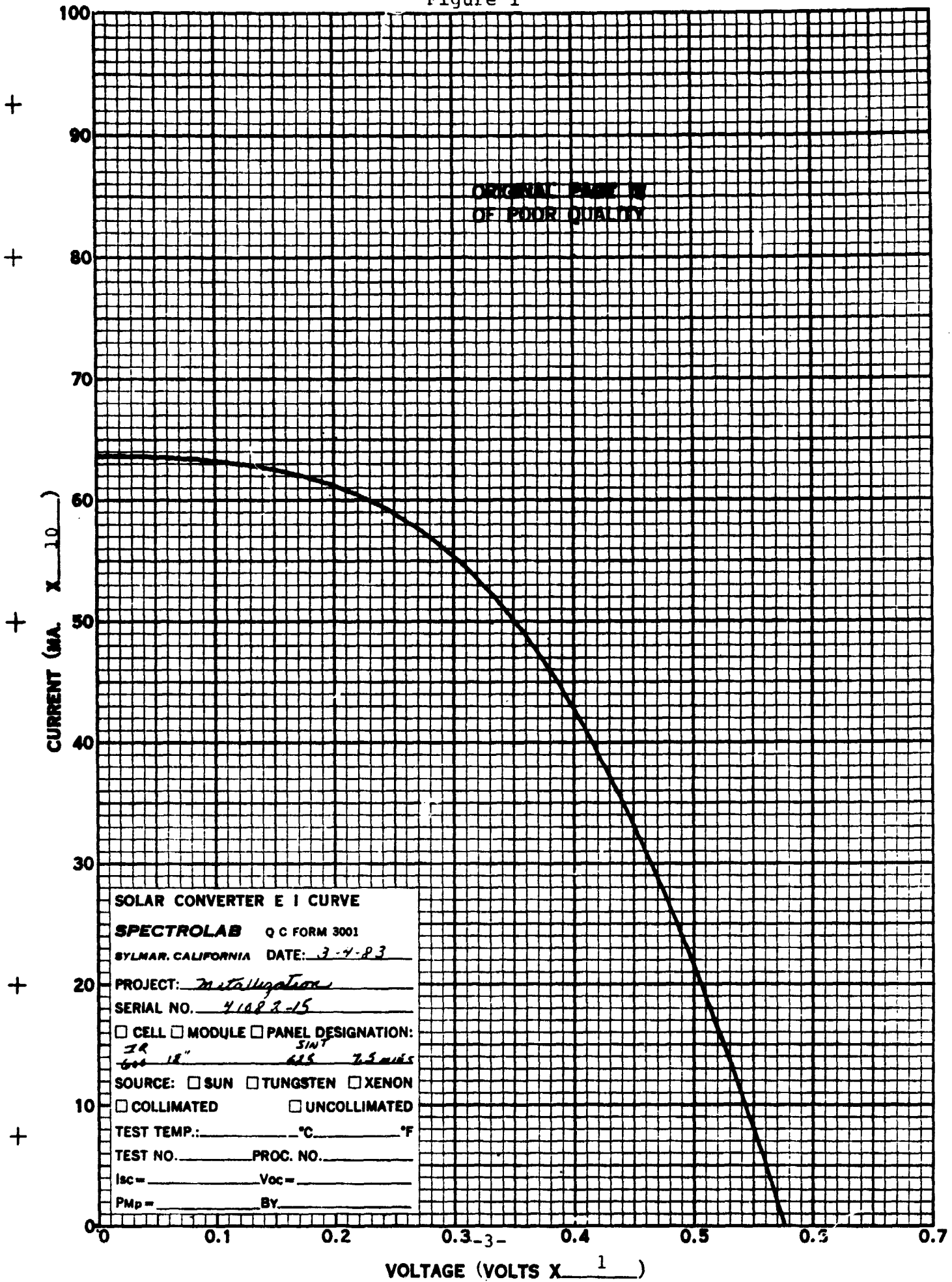


Figure 2

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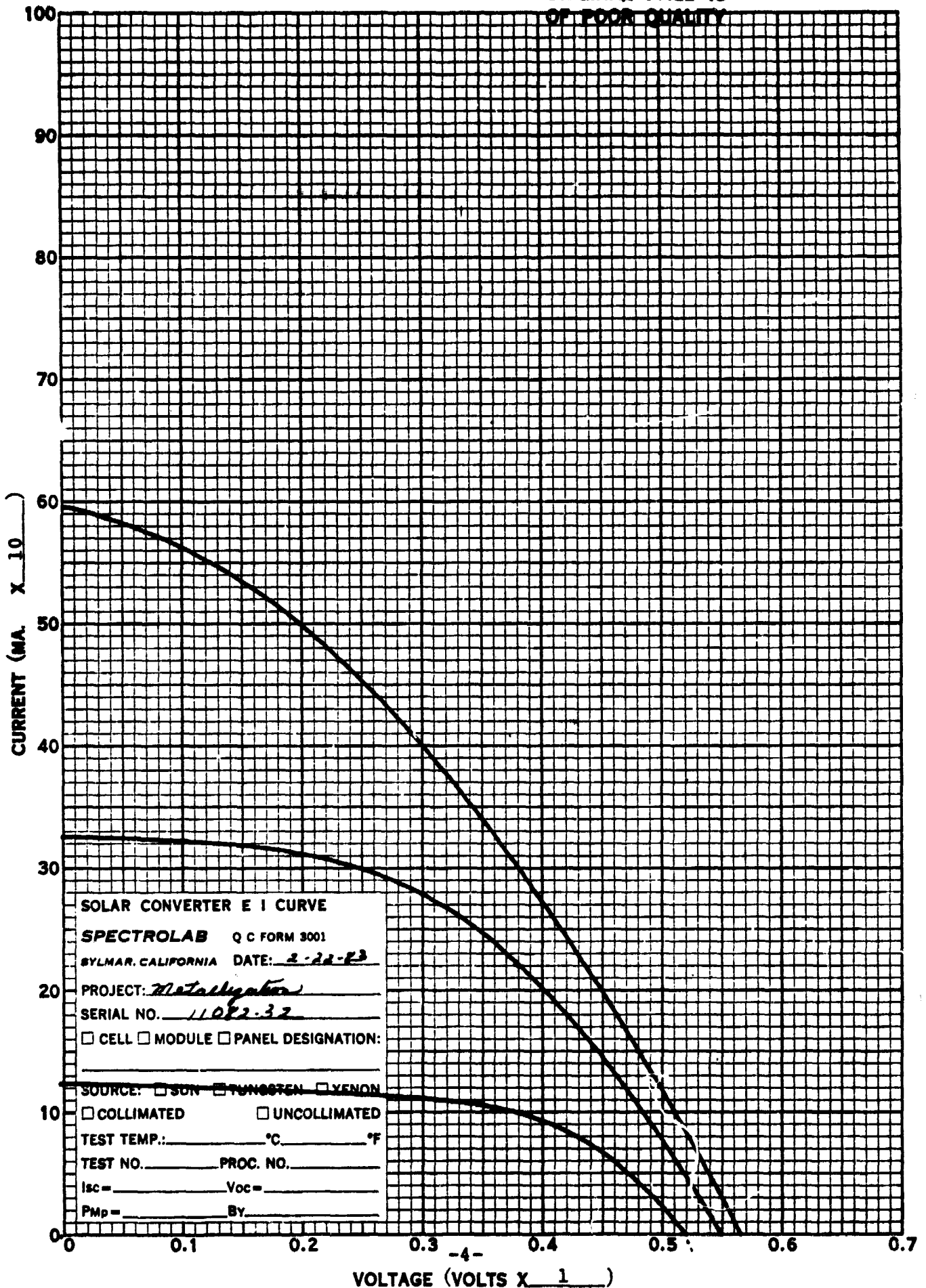
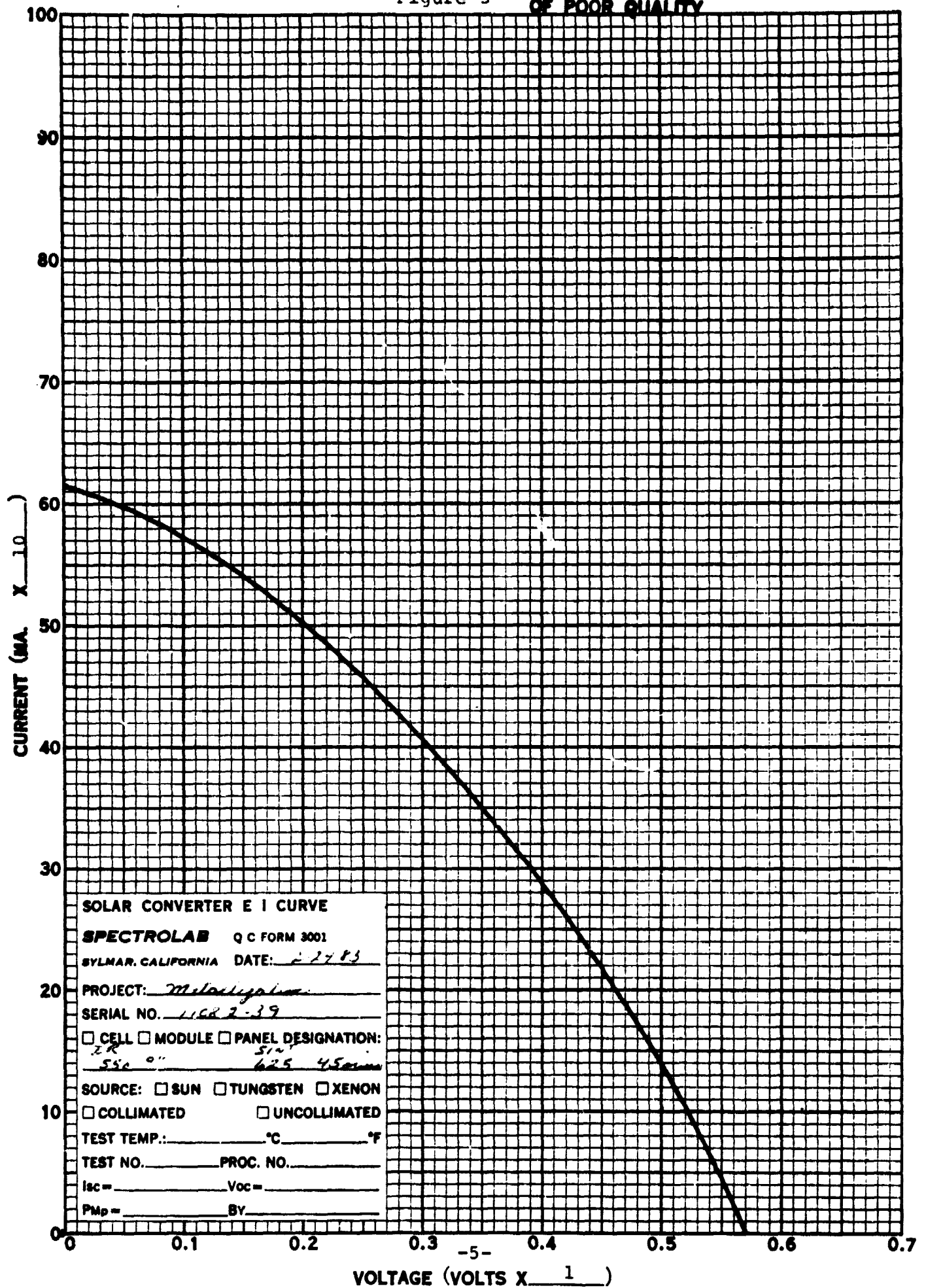




Figure 3

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index of refraction of  $\sim 1.95$ . The reflected color varied with increasing thickness as follows: green bronze, bronze, purple, blue. The cells were reduced using hydrogen at  $600^{\circ}\text{C}$ . The hydrogen firing also reduced the ITO causing a milky appearance on the cells. Air firing of the cell brought back some of the color of the film and improved cell performance as is shown in Figure 4. Attempts to fire the cells at  $650^{\circ}\text{C}$  led to severe shunting, Figure 5. The particle-to-particle adhesion for the ITO cells was still not adequate for soldering.

Several cells were made by screen printing silver paste over the ITO. Figure 6 shows these cells as compared with a conventionally AR coated silver cell. ITO does not appear to be as effective an AR coating as the conventional  $\text{SiO}_2$ . This may be due to incorrect thickness, lower index of refraction, or absorption in the ITO.

A group of cells were reduced sequentially in CO and hydrogen and vice versa. These cells showed excellent electrical characteristics similar to  $\text{H}_2$  reduced cells but were still unsolderable.

In another experiment a paste was made by adding 3% #3347 silver paste (Thick Film Systems) to the Type F paste. This paste was then used with both CO and  $\text{H}_2$  reductions. These cells were also unsolderable.

Figure 4

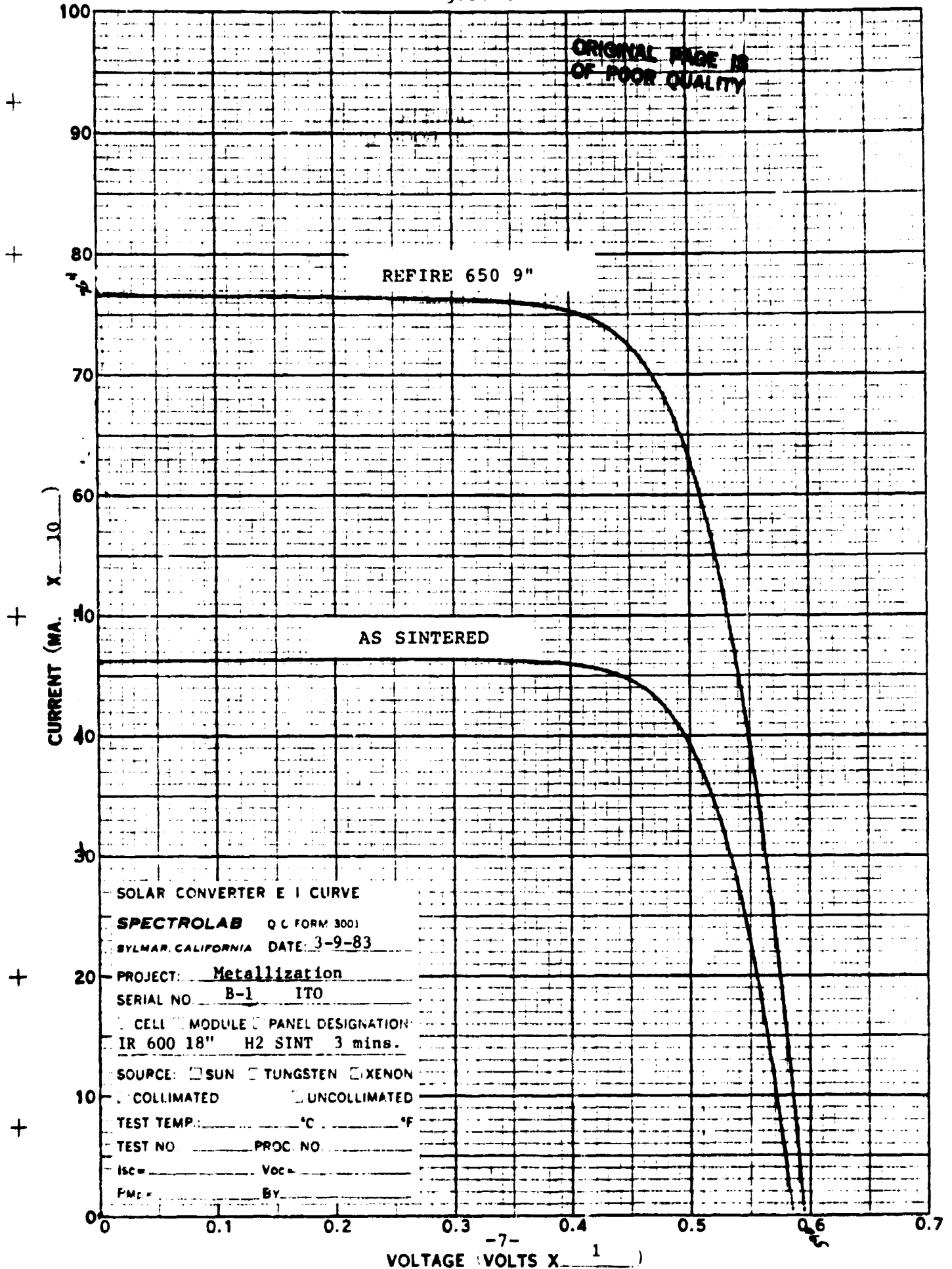
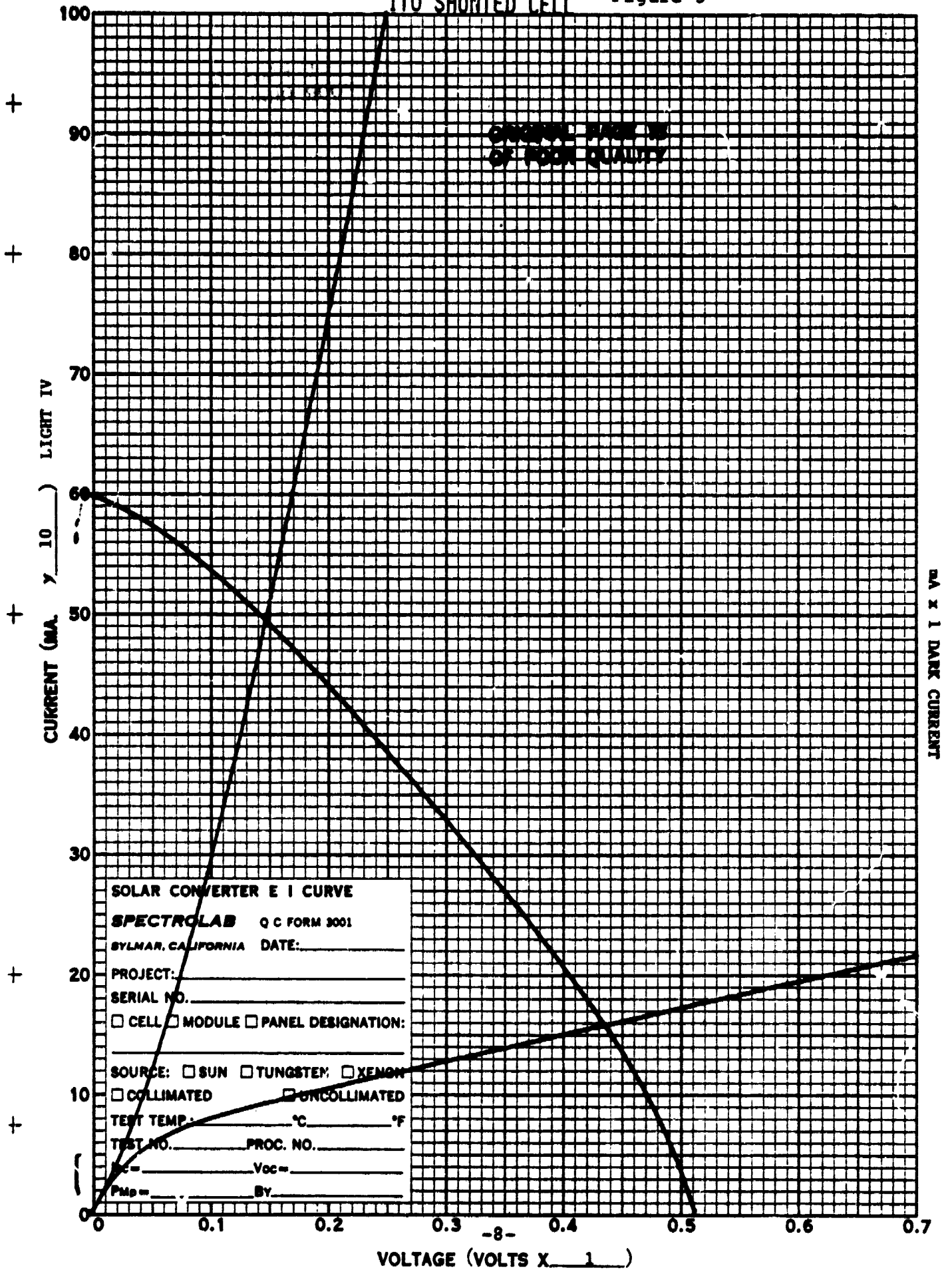


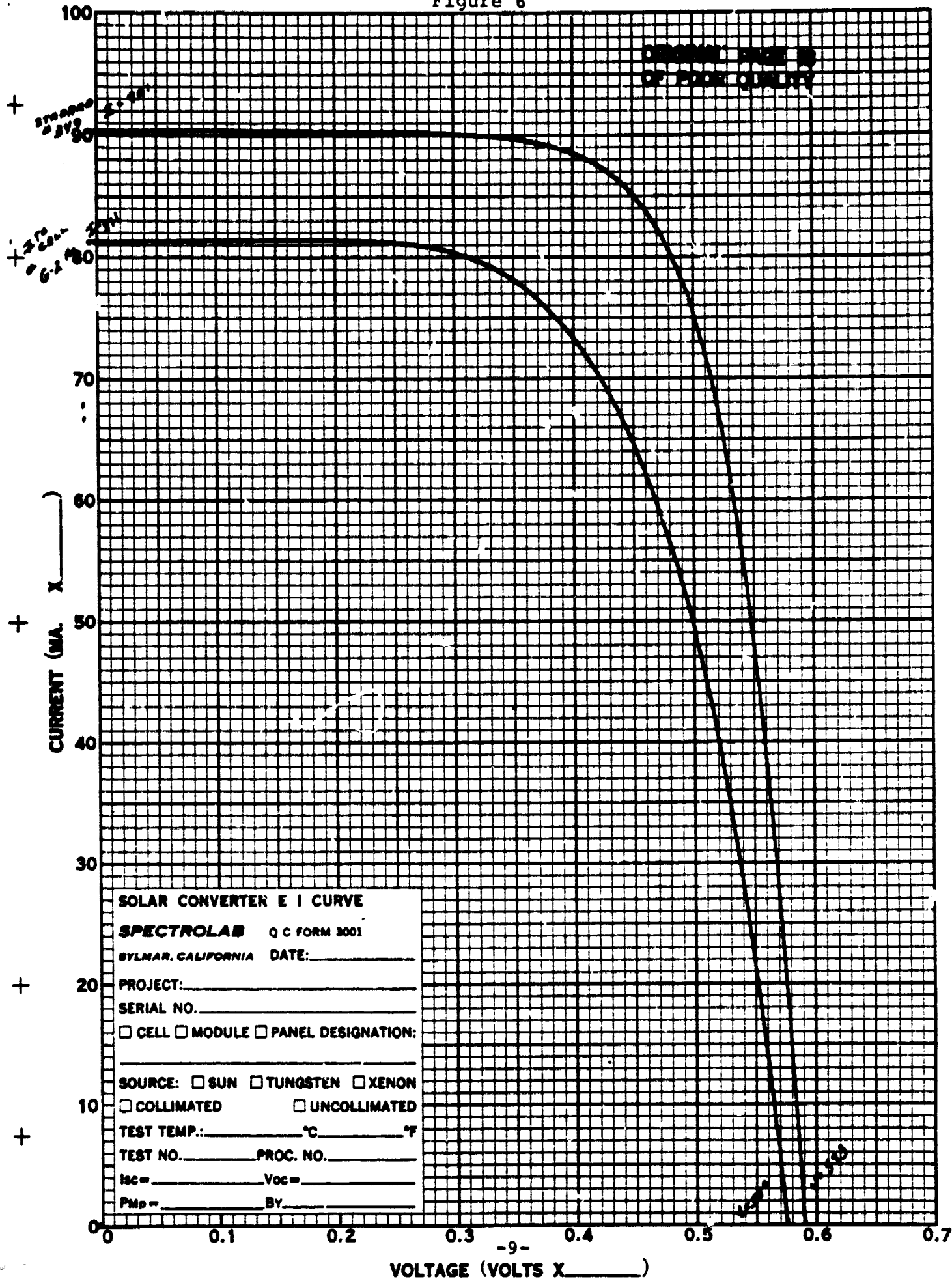
Figure 5

ITO SHUNTED CELL



MA x 1 DARK CURRENT

Figure 6



### Section 3.0

#### CONCLUSIONS AND RECOMMENDATIONS

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Work will continue on solving the adhesion problem between the pastes and silicon which preclude the successful solder of interconnects to the cell.

## Section 4.0

### ACTIVITIES PROJECTION

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A revised program plan and milestone chart was developed concurrently with JPL personnel. This milestone chart follows:

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